



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ\text{C}$
60V	13m Ω @ $V_{GS} = 10\text{V}$	10.3A
	18m Ω @ $V_{GS} = 4.5\text{V}$	8.8A

Features and Benefits

- Low $R_{DS(ON)}$ —Ensures On-state Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of Board Area Occupied by SO-8 Enabling Smaller End Product

Description

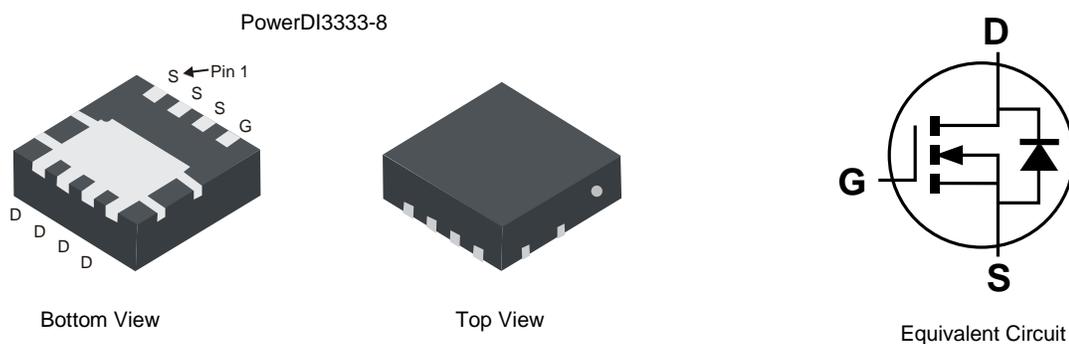
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe
Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.072 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	T _A = +25°C	10.3	A
	T _A = +70°C	8.3	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	T _C = +25°C	45	A
	T _C = +100°C	28	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	3	A
Avalanche Current, L = 0.1mH	I _{AS}	33.3	A
Avalanche Energy, L = 0.1mH	E _{AS}	56.8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady state	123
		t < 10s	69
Total Power Dissipation (Note 6)	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady state	60
		t < 10s	34
Total Power Dissipation (Note 6)	P _D	40	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	3.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	1.8	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9.3	13	mΩ	V _{GS} = 10V, I _D = 10A
		—	12.3	18		V _{GS} = 4.5V, I _D = 8A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	2577	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	162	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	132	—	pF	
Gate Resistance	R _g	—	0.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	26.6	—	nC	V _{DS} = 30V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	55.4	—	nC	
Gate-Source Charge	Q _{gs}	—	9.3	—	nC	
Gate-Drain Charge	Q _{gd}	—	12.6	—	nC	
Turn-On Delay Time	t _{D(on)}	—	6.2	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _G = 3Ω, I _D = 10A
Turn-On Rise Time	t _r	—	9.9	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	27.6	—	ns	
Turn-Off Fall Time	t _f	—	11.7	—	ns	
Body Diode Reverse Recovery Time	t _{rr}	—	9.4	—	nS	I _F = 10A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{rr}	—	18.6	—	nC	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

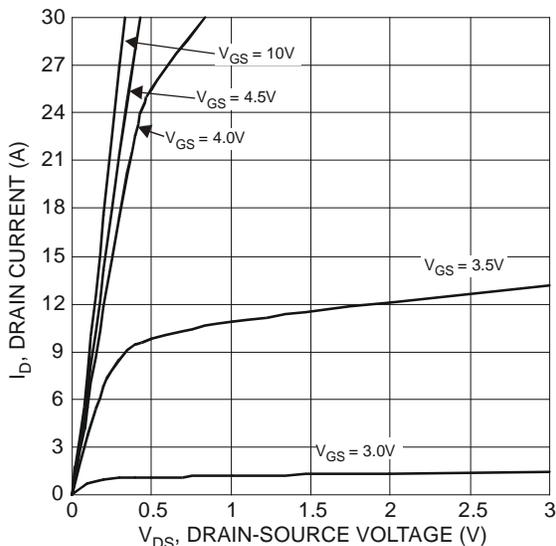


Figure 1 Typical Output Characteristics

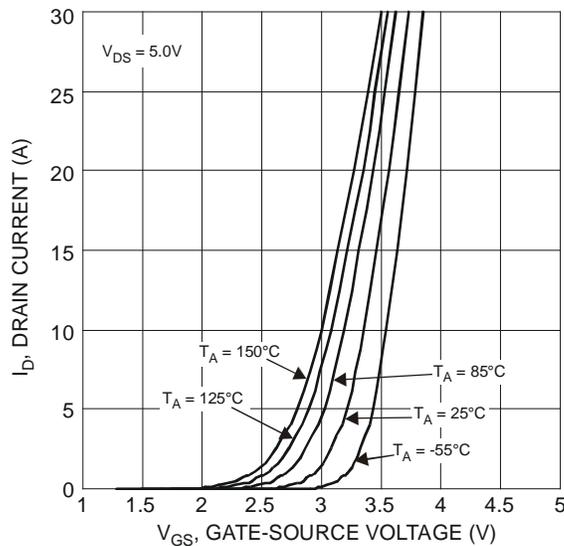


Figure 2 Typical Transfer Characteristics

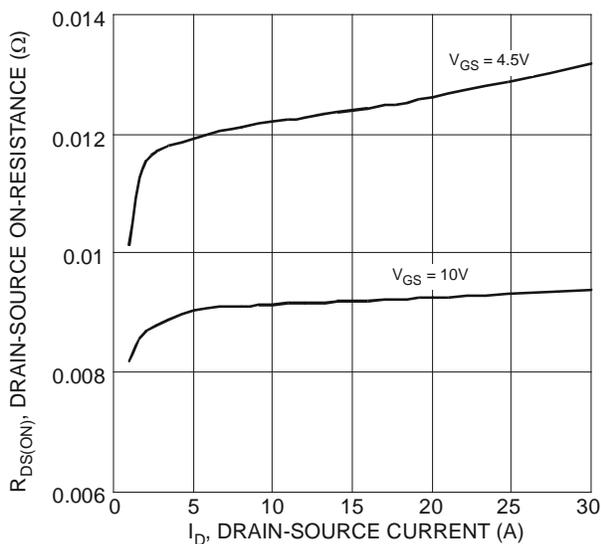


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

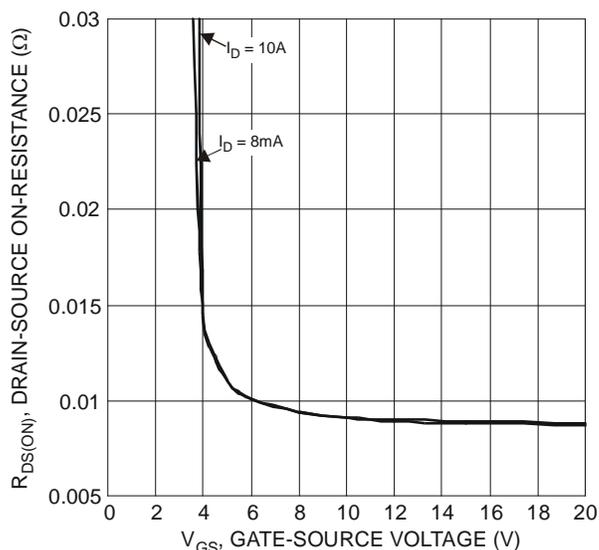


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

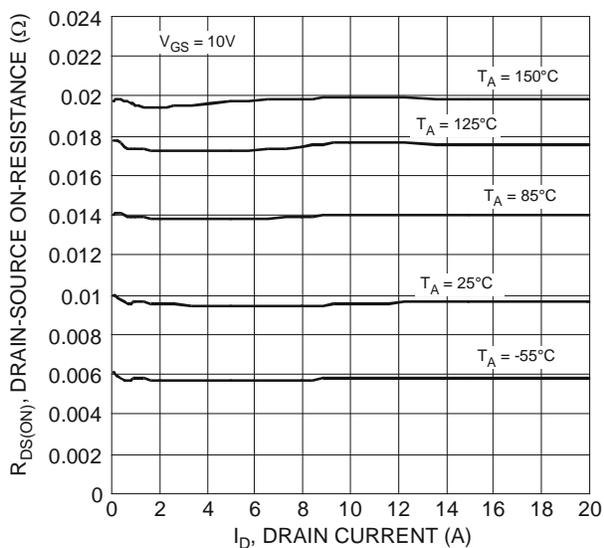


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

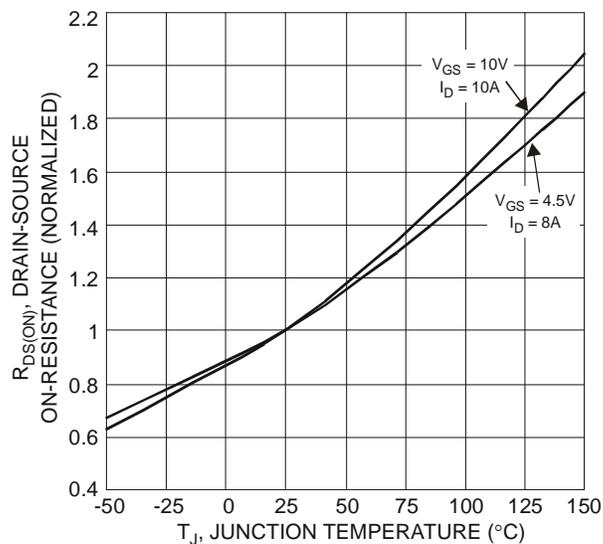


Figure 6 On-Resistance Variation with Temperature

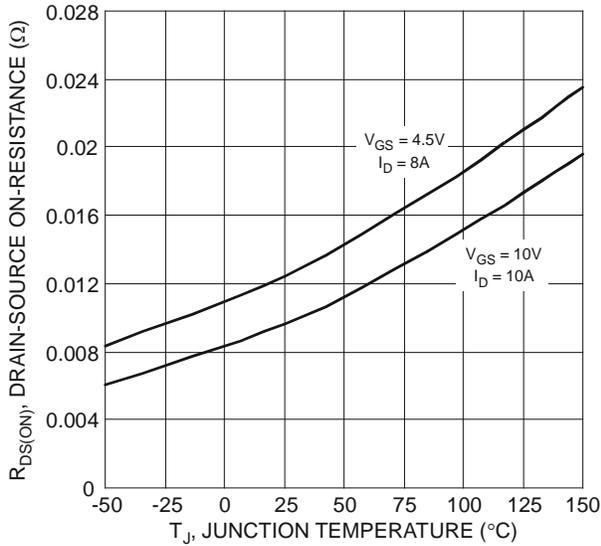


Figure 7 On-Resistance Variation with Temperature

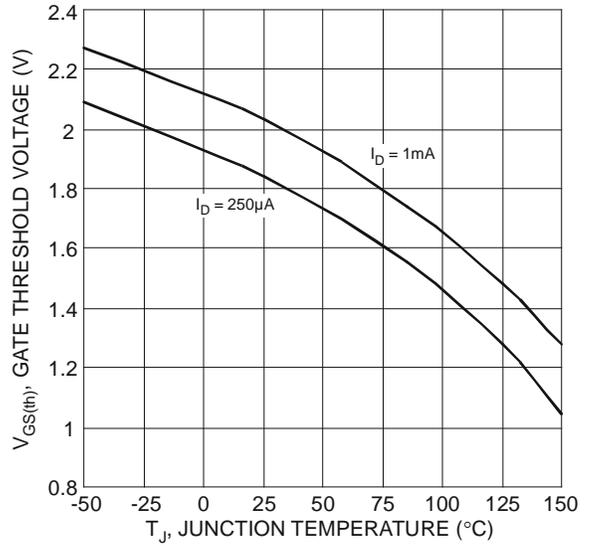


Figure 8 Gate Threshold Variation vs. Ambient Temperature

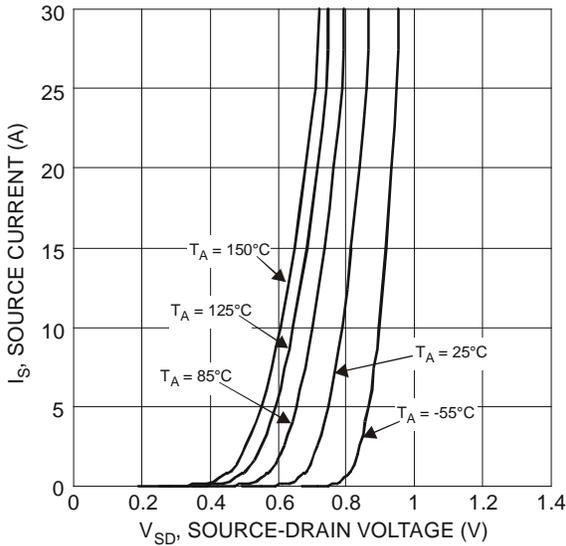


Figure 9 Diode Forward Voltage vs. Current

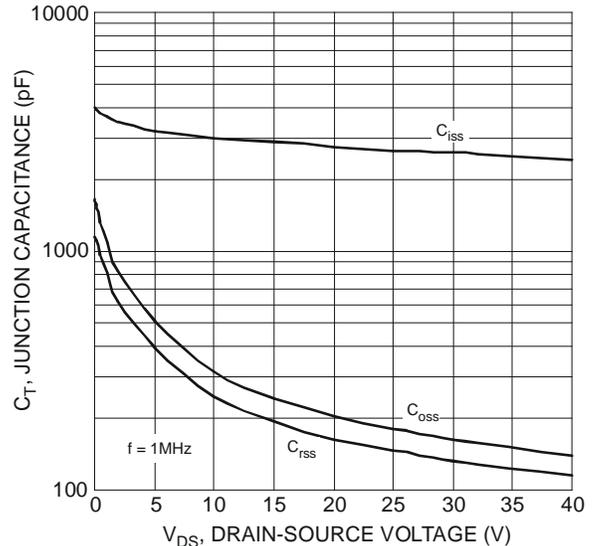


Figure 10 Typical Junction Capacitance

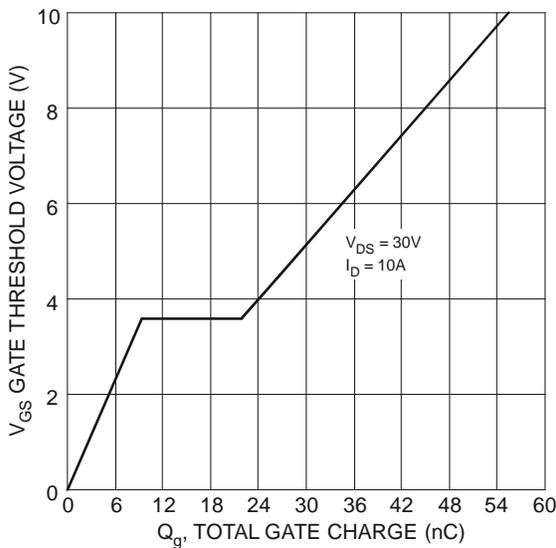


Figure 11 Gate Charge

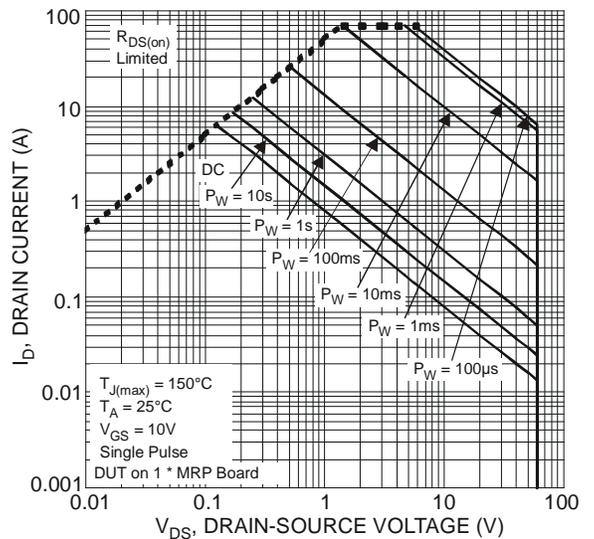
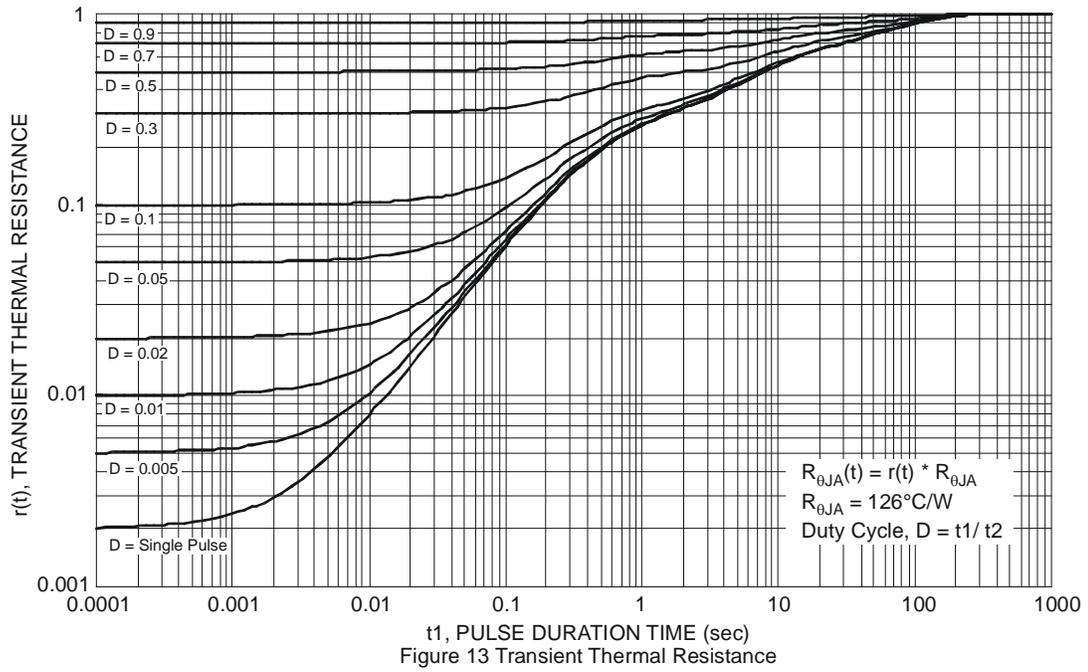
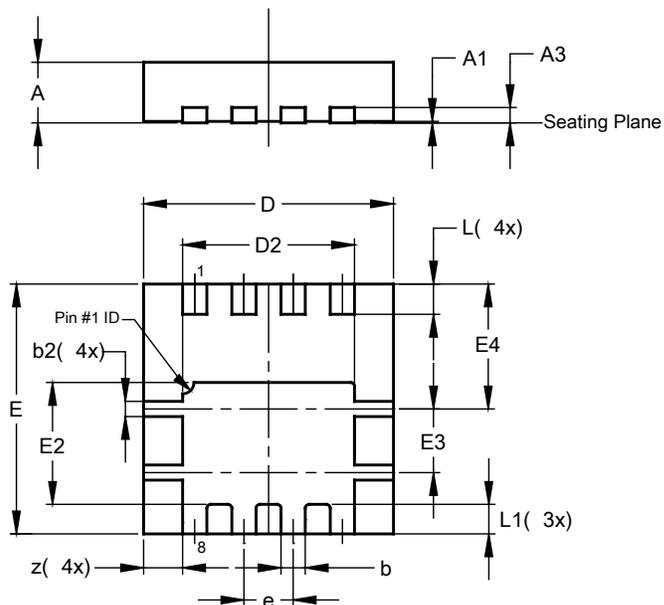


Figure 12 SOA, Safe Operation Area

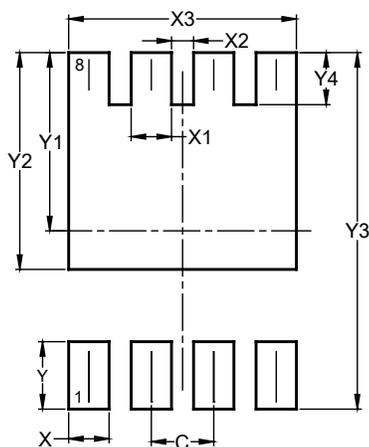


Package Outline Dimensions

PowerDI3333-8


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	—	—	0.65
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

PowerDI3333-8


Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540